# NSN 5961-00-865-7539

Transistor - Page 1 of 2



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Inclosure Material:

Metal

**Overall Length:** 

0.406 inches

# **Overall Diameter:**

0.828 inches

# Mounting Facility Quantity:

1

#### Internal Configuration:

Junction contact

#### Electrode Internally-electrically Connected To Case:

Collector

#### **Mounting Method:**

Threaded stud

#### Features Provided:

#### Hermetically sealed case

#### **Overall Width Across Flats:**

0.865 inches

# Thread Size:

0.312 inches

#### Semiconductor Material:

Silicon

#### Voltage Rating In Volts Per Characteristic:

125.0 breakdown voltage, collector-to-base, emitter open and 60.0 breakdown voltage, collector-to-emitter, base open and 6.0

breakdown voltage, emitter-to-base, collector open

#### **Current Rating Per Characteristic:**

Between 10.00 amperes source cutoff current and 20.00 amperes source cutoff current

#### Power Rating Per Characteristic:

150.0 watts small-signal input power, common-collector

# Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

# **Special Features:**

Junction pattern arrangement: npn

# **Thread Series Designator:**

Unf

# Terminal Type And Quantity:

3 tab, solder lug

Shelf Life:

N/a

# Unit Of Measure:

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# Demilitarization:

No

# **NSN 5961-00-865-7539** Transistor - Page 2 of 2

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